

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

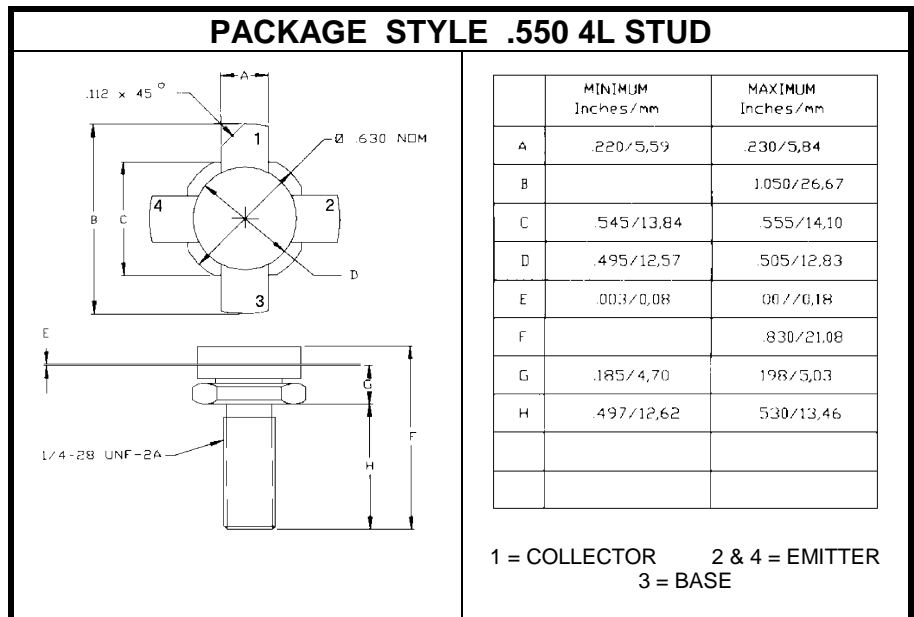
The **ASI THX15C** is a Common Emitter Device Designed for High Linearity Class A/AB HF Applications.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	10 A
<b>V<sub>CB</sub></b>	110 V
<b>P<sub>DISS</sub></b>	233 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	0.75 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 100 mA	55			<b>V</b>
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 100 mA      V <sub>BE</sub> = 0 V	110			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 mA	110			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 60 V      V <sub>BE</sub> = 0 V			5.0	<b>mA</b>
<b>I<sub>CEO</sub></b>	V <sub>CE</sub> = 30 V			5.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 6.0 V      I <sub>C</sub> = 1.4 A	22.5		27.0	<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 50 V      f = 1.0 MHz			220	<b>pF</b>
<b>P<sub>g</sub></b>		14			<b>dB</b>
<b>IMD<sub>3</sub></b>	V <sub>CE</sub> = 50 V      I <sub>cq</sub> = 100 mA		-37	-30	<b>dBc</b>
<b>η<sub>C</sub></b>	f = 30 MHz      P <sub>out</sub> = 150 W (PEP)	37	45		<b>%</b>